



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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UNR521x Series (UN521x Series)

Silicon NPN epitaxial planar type

For digital circuits

■ Features

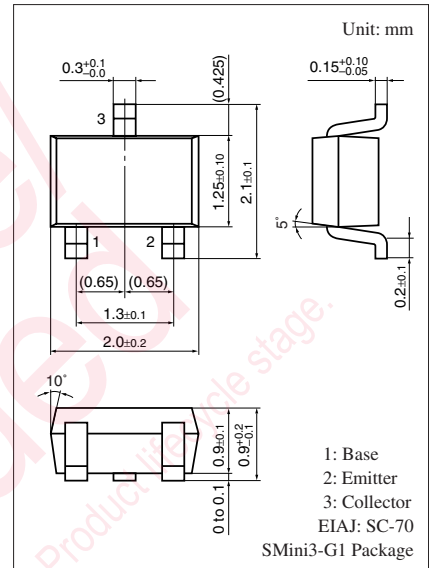
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- S-Mini type package, allowing automatic insertion through the tape packing and magazine packing

■ Resistance by Part Number

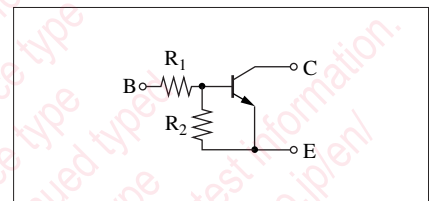
	Marking symbol (R ₁)	(R ₂)
• UNR5210 (UN5210)	8L	47 kΩ —
• UNR5211 (UN5211)	8A	10 kΩ 10 kΩ
• UNR5212 (UN5212)	8B	22 kΩ 22 kΩ
• UNR5213 (UN5213)	8C	47 kΩ 47 kΩ
• UNR5214 (UN5214)	8D	10 kΩ 47 kΩ
• UNR5215 (UN5215)	8E	10 kΩ —
• UNR5216 (UN5216)	8F	4.7 kΩ —
• UNR5217 (UN5117)	8H	22 kΩ —
• UNR5218 (UN5218)	8I	0.51 kΩ 5.1 kΩ
• UNR5219 (UN5219)	8K	1 kΩ 10 kΩ
• UNR521D (UN521D)	8M	47 kΩ 10 kΩ
• UNR521E (UN521E)	8N	47 kΩ 22 kΩ
• UNR521F (UN521F)	8O	4.7 kΩ 10 kΩ
• UNR521K (UN521K)	8P	10 kΩ 4.7 kΩ
• UNR521L (UN521L)	8Q	4.7 kΩ 4.7 kΩ
• UNR521M (UN521M)	EL	2.2 kΩ 47 kΩ
• UNR521N (UN521N)	EX	4.7 kΩ 47 kΩ
• UNR521T (UN521T)	EZ	22 kΩ 47 kΩ
• UNR521V (UN521V)	FD	2.2 kΩ 2.2 kΩ
• UNR521Z (UN521Z)	FF	4.7 kΩ 22 kΩ

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	50	V
Collector current	I _C	100	mA
Total power dissipation	P _T	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Internal Connection



(Note) The part numbers in the parenthesis show conventional part number.

Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)		V_{CBO}	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	50			V
Collector-emitter voltage (Base open)		V_{CEO}	$I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$	50			V
Collector-base cutoff current (Emitter open)		I_{CBO}	$V_{\text{CB}} = 50 \text{ V}, I_{\text{E}} = 0$			0.1	μA
Collector-emitter cutoff current (Base open)		I_{CEO}	$V_{\text{CE}} = 50 \text{ V}, I_{\text{B}} = 0$			0.5	
Emitter-base cutoff current (Collector open)	UNR5210/5215/5216/5217	I_{EBO}	$V_{\text{EB}} = 6 \text{ V}, I_{\text{C}} = 0$			0.01	mA
	UNR5213					0.1	
	UNR5212/5214/521D/ 521E/521M/521N/521T					0.2	
	UNR521Z					0.4	
	UNR5211					0.5	
	UNR521F/521K					1.0	
	UNR5219					1.5	
	UNR5218/521L/521V					2.0	
Forward current transfer ratio	UNR521V	h_{FE}	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 5 \text{ mA}$	6		20	—
	UNR5218/521K/521L			20			
	UNR5219/521D/521F			30			
	UNR5211			35			
	UNR5212/521E			60			
	UNR521Z			60	200		
	UNR5213/5214/521M			80			
	UNR521N/521T			80	400		
	UNR5210*/5215*/5216*/5217*			160	460		
Collector-emitter saturation voltage		$V_{\text{CE(sat)}}$	$I_{\text{C}} = 10 \text{ mA}, I_{\text{B}} = 0.3 \text{ mA}$			0.25	V
UNR521V				$I_{\text{C}} = 10 \text{ mA}, I_{\text{B}} = 1.5 \text{ mA}$			
Output voltage high-level		V_{OH}	$V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 0.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level		V_{OL}	$V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 2.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$			0.2	V
UNR5213/521K			$V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 3.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$				
UNR521D			$V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 10 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$				
UNR521E			$V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 6.0 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$				
Transition frequency		f_{T}	$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Input resistance	UNR5218	R_{I}		-30%	0.51	+30%	$\text{k}\Omega$
	UNR5219				1.0		
	UNR521M/521V				2.2		
	UNR5216/521F/521L/521N UNR521Z				4.7		
	UNR5211/5214/5215/521K				10		
	UNR5212/5217/521T				22		
	UNR5210/5213/521D/521E				47		

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

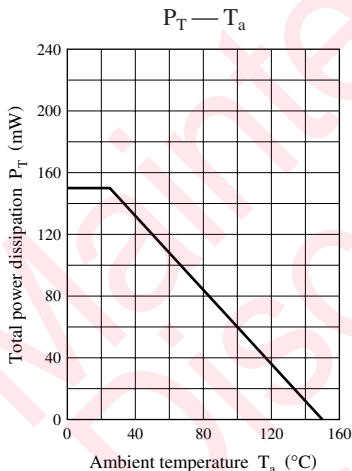
2. *: Rank classification

Rank	Q	R	S	No-rank
h_{FE}	160 to 260	210 to 340	290 to 460	160 to 460

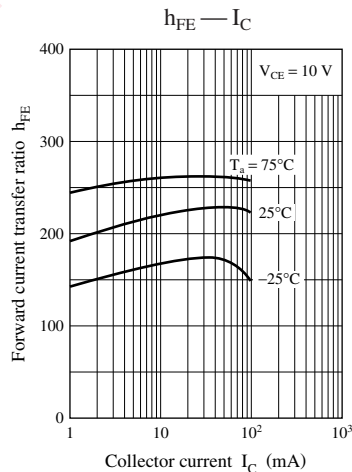
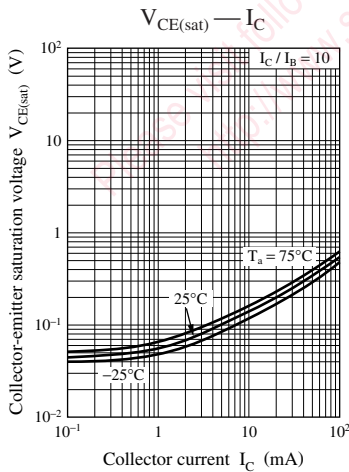
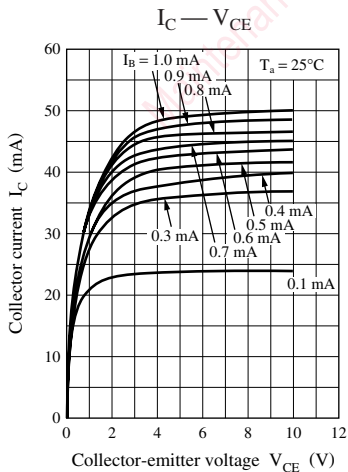
■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

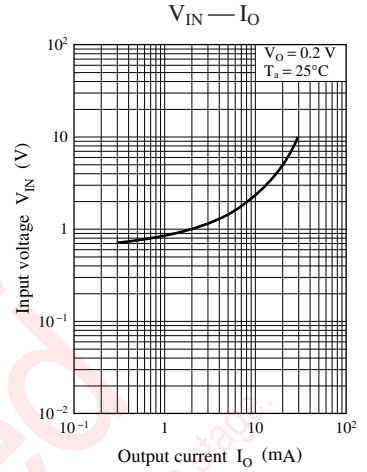
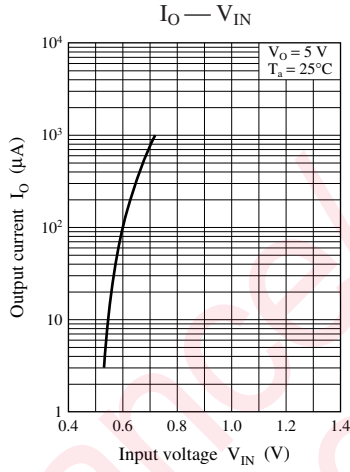
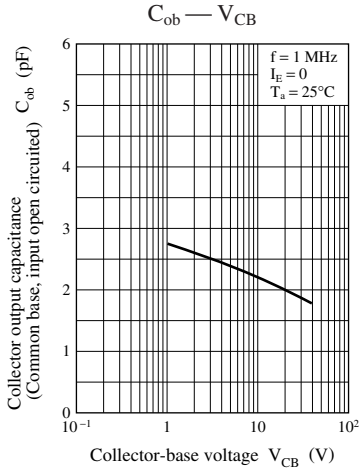
	Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Resistance ratio	UNR521M	R_1/R_2			0.047		—
	UNR521N				0.1		
	UNR5218/5219				0.08	0.10	0.12
	UNR521Z					0.21	
	UNR5214				0.17	0.21	0.25
	UNR521T					0.47	
	UNR521F				0.37	0.47	0.57
	UNR521V					1.0	
	UNR5211/5212/5213/521L				0.8	1.0	1.2
	UNR521K				1.70	2.13	2.60
	UNR521E				1.70	2.14	2.60
	UNR521D				3.7	4.7	5.7

Common characteristics chart

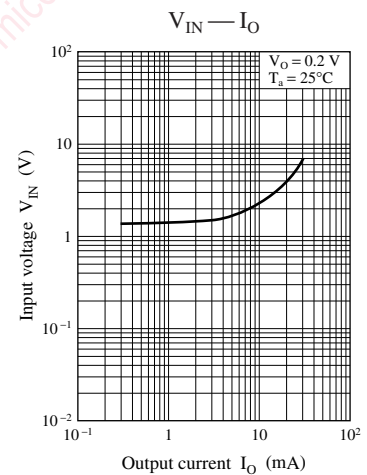
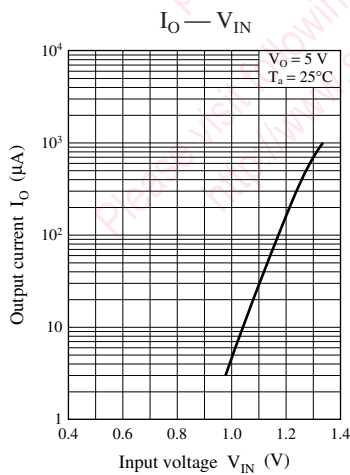
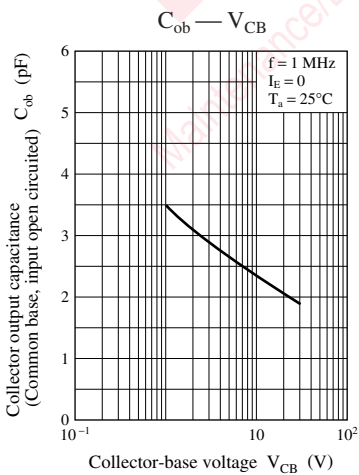
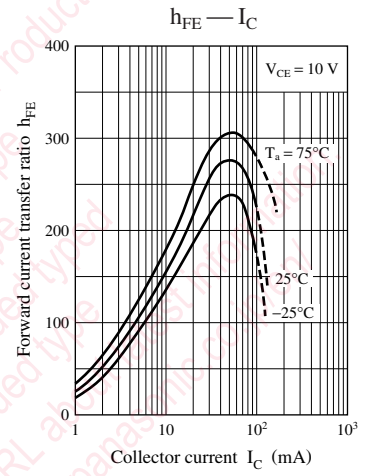
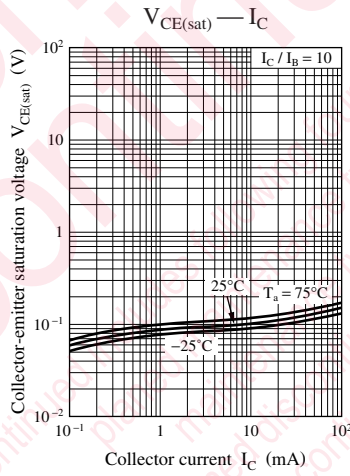
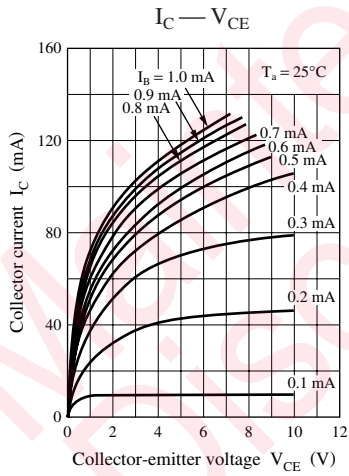


Characteristics charts of UNR5210

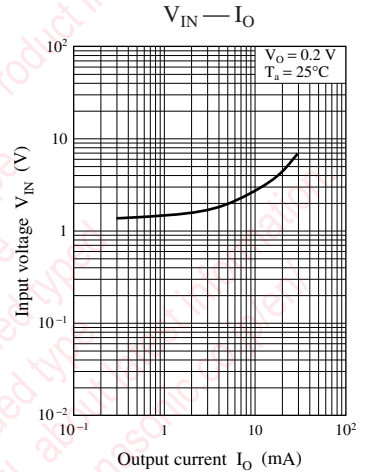
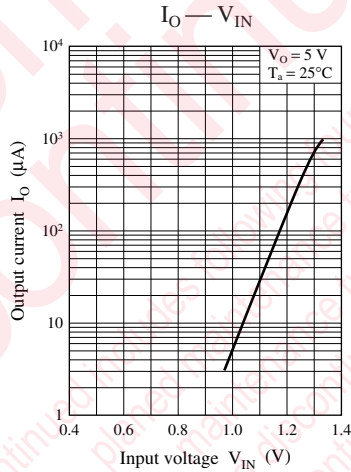
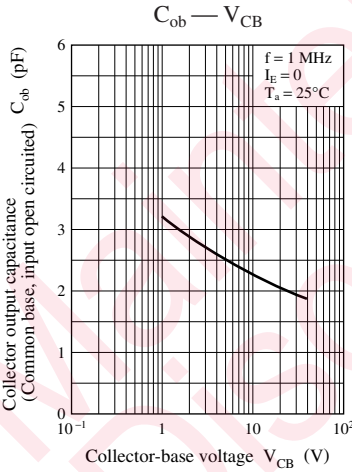
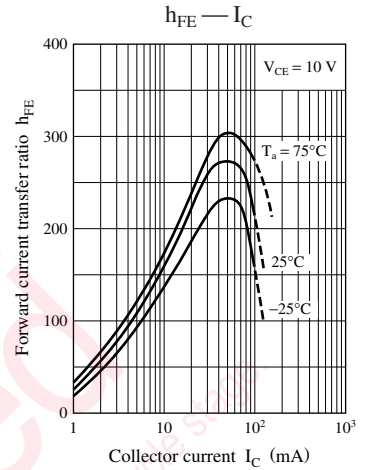
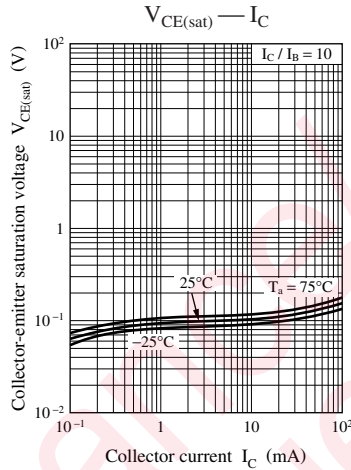
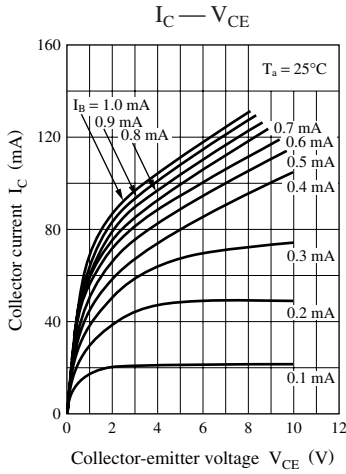




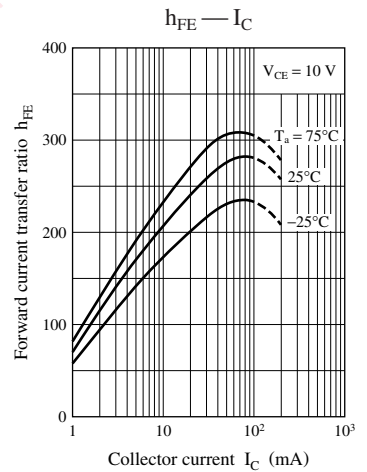
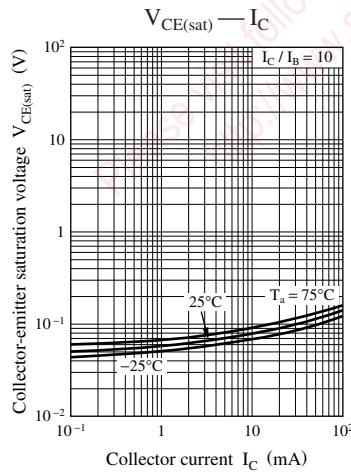
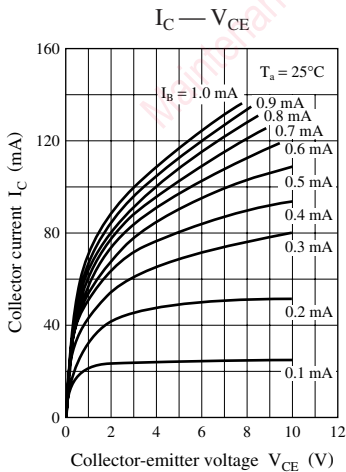
Characteristics charts of UNR5211

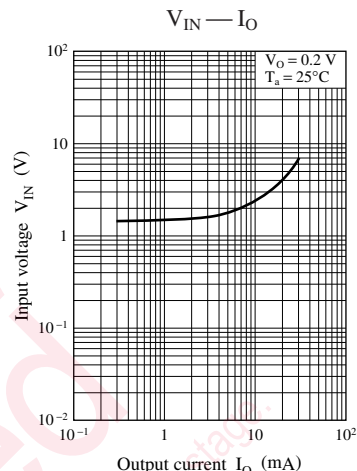
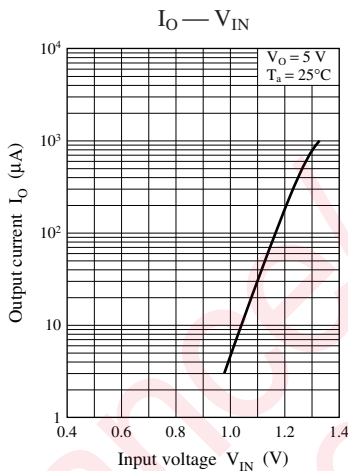
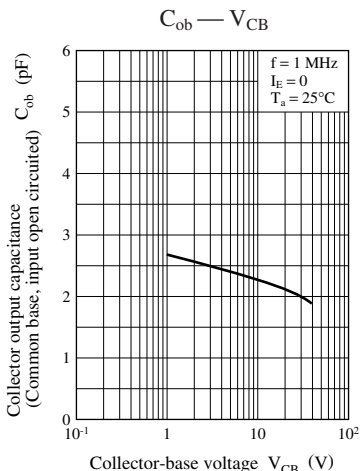


Characteristics charts of UNR5212

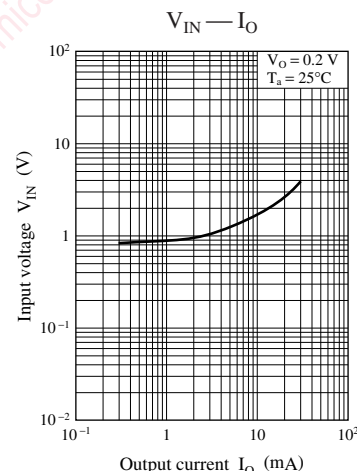
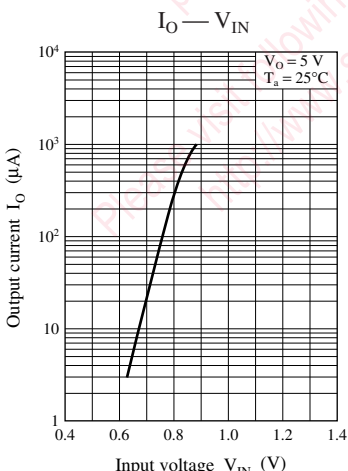
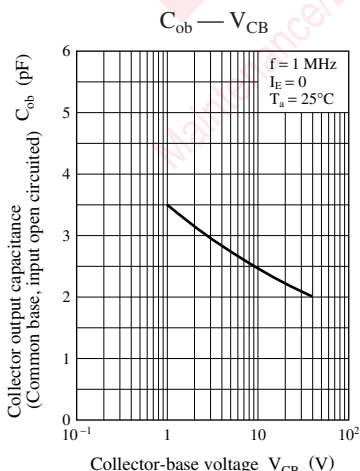
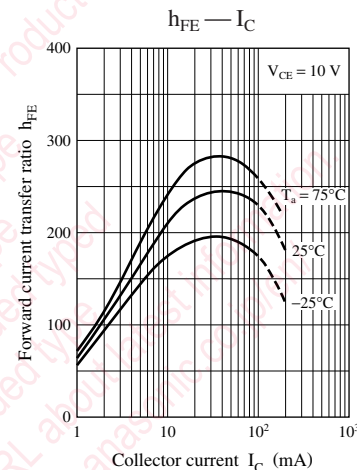
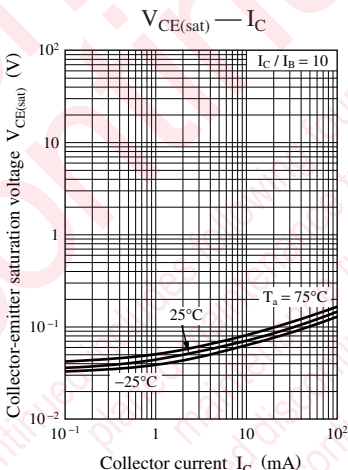
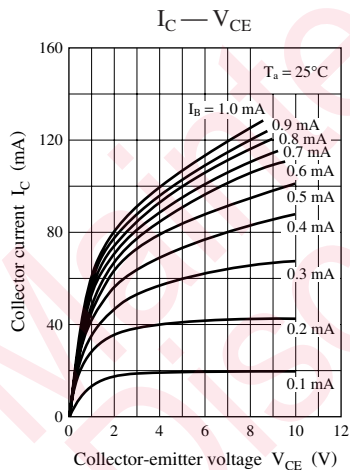


Characteristics charts of UNR5213

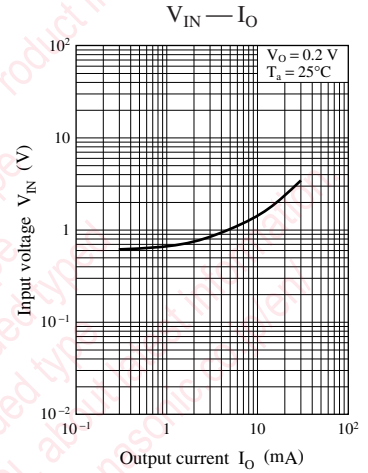
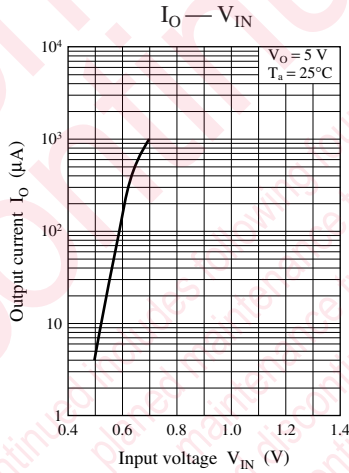
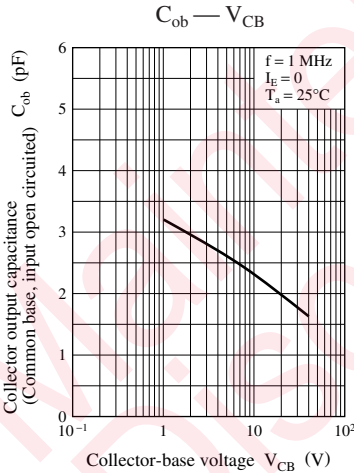
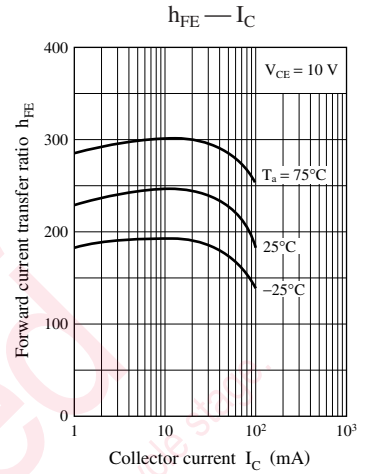
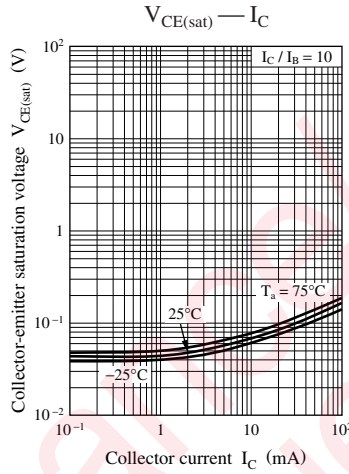
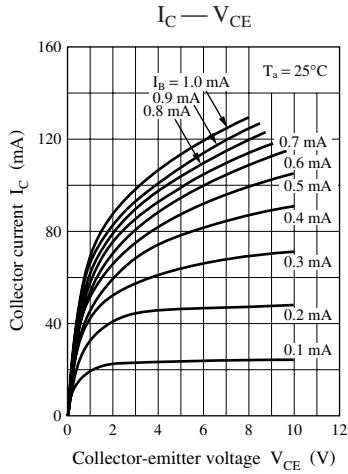




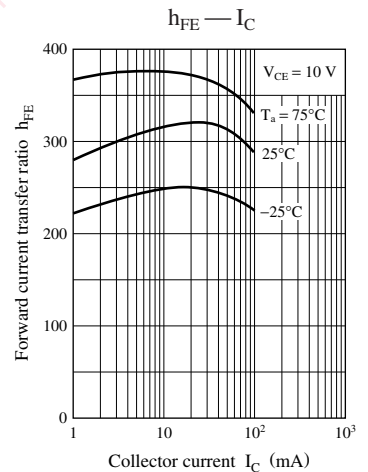
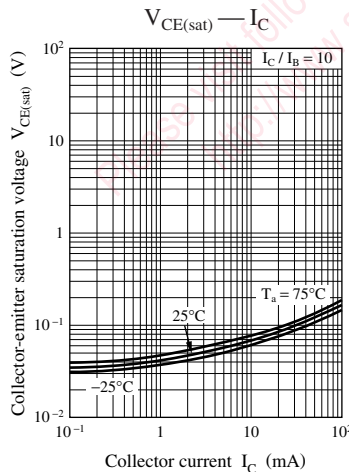
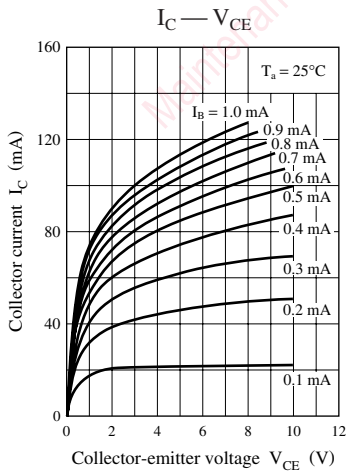
Characteristics charts of UNR5214

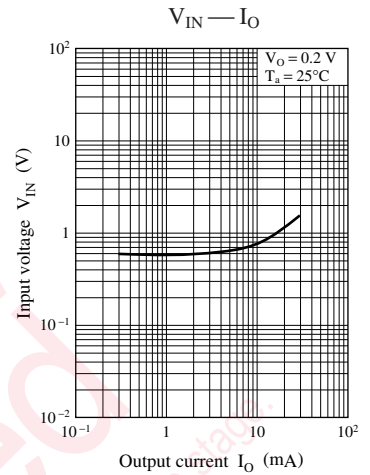
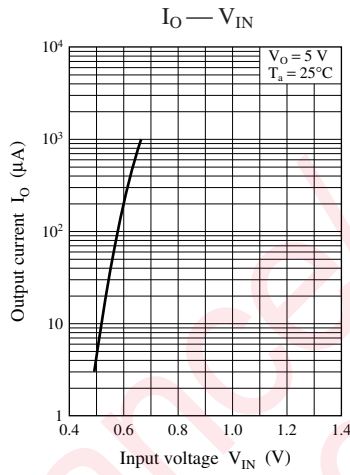
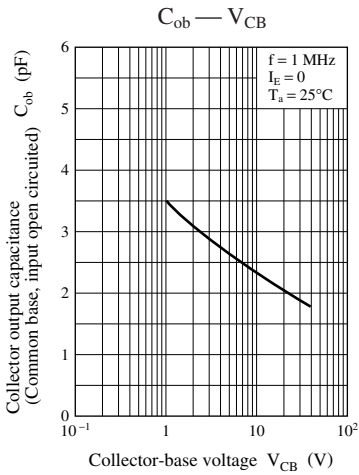


Characteristics charts of UNR5215

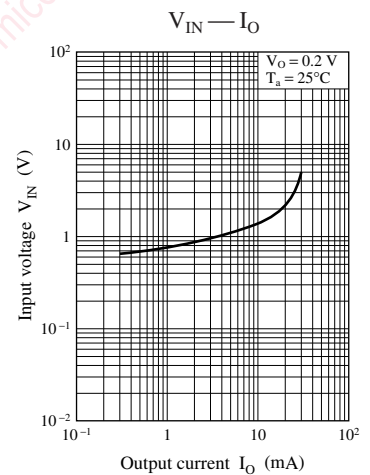
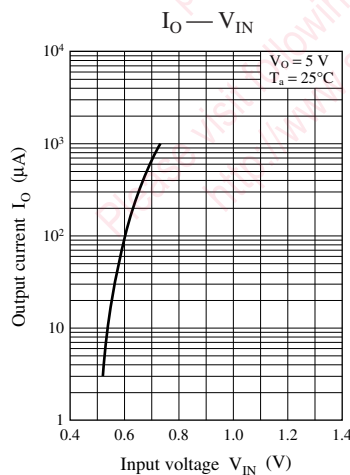
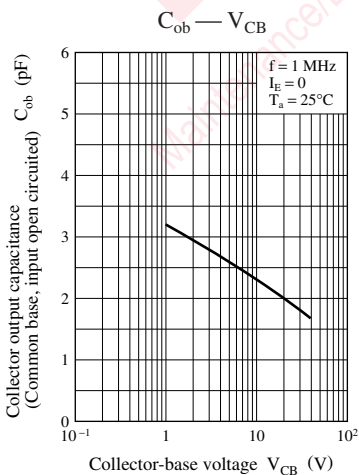
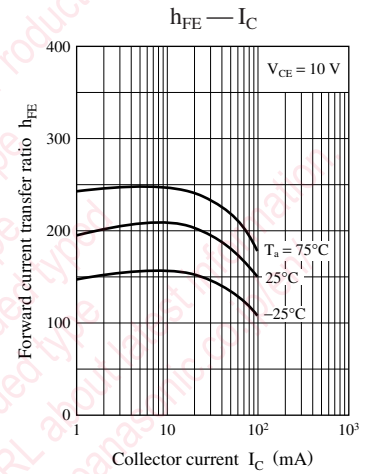
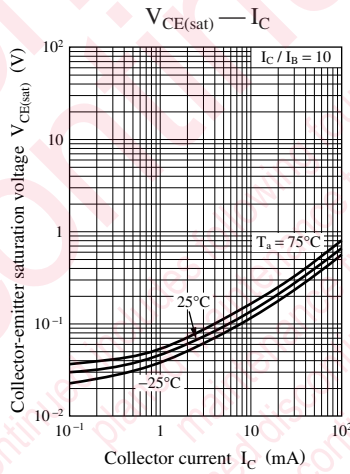
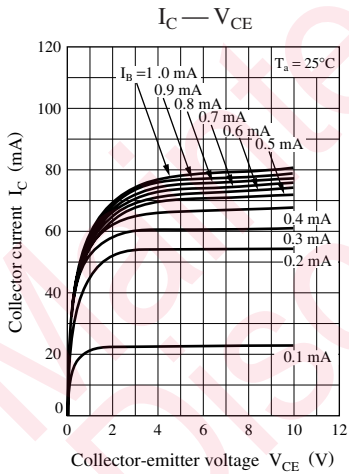


Characteristics charts of UNR5216

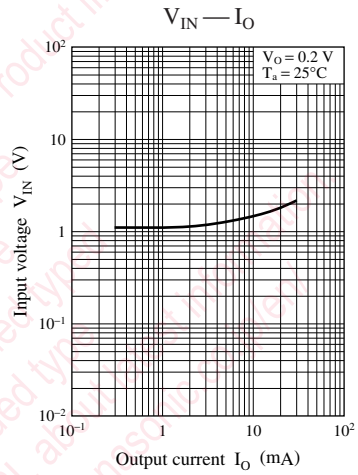
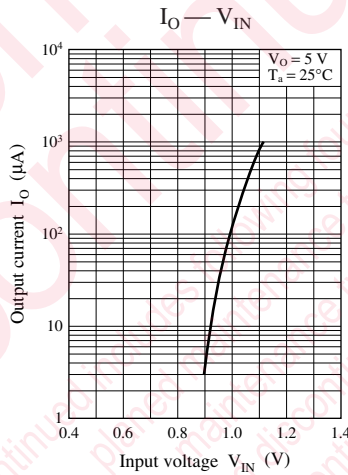
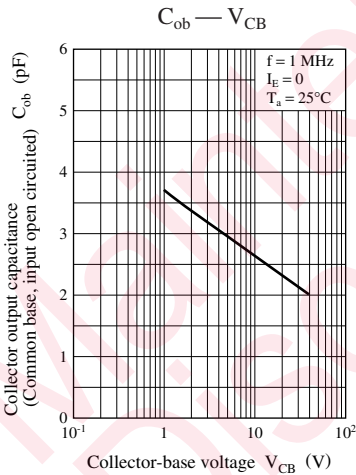
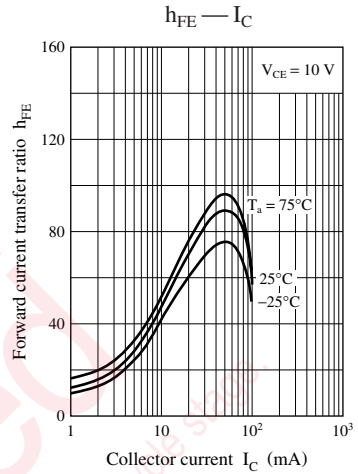
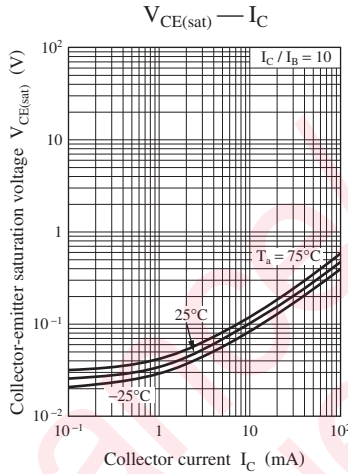
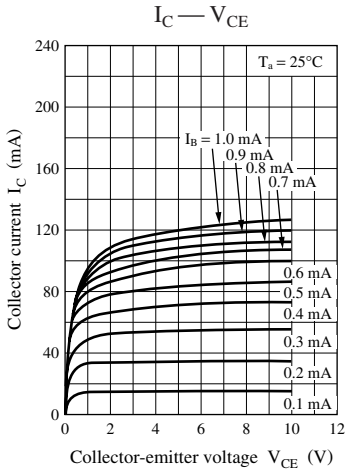




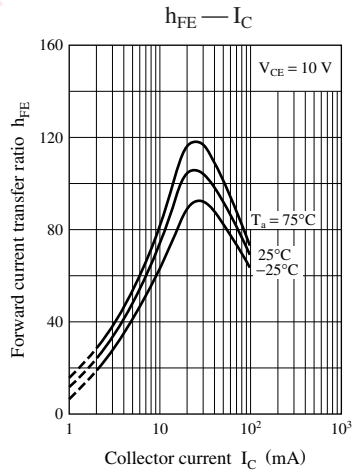
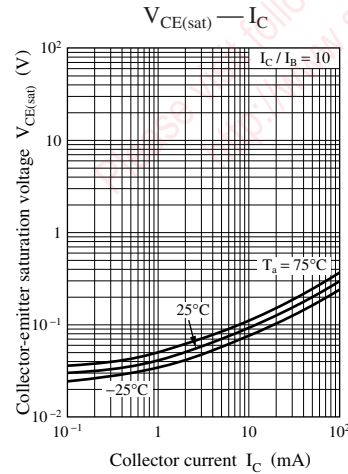
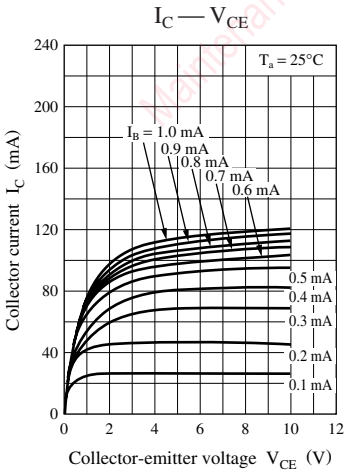
Characteristics charts of UNR5217

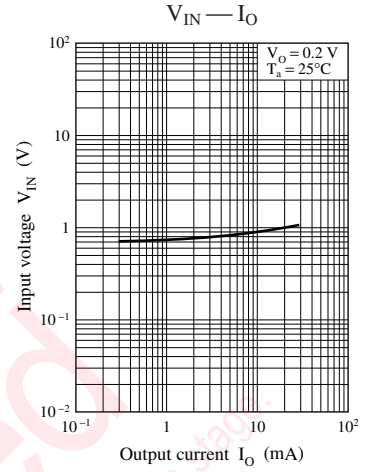
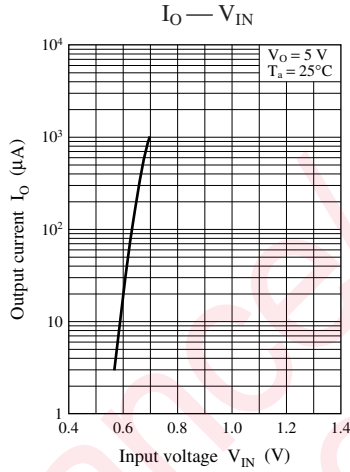
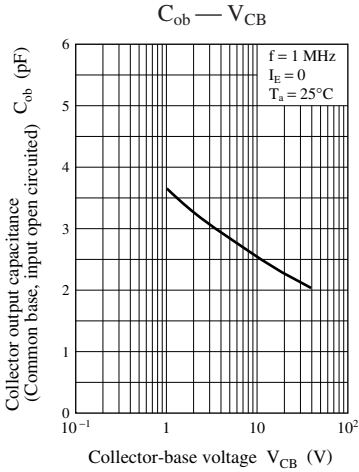


Characteristics charts of UNR5218

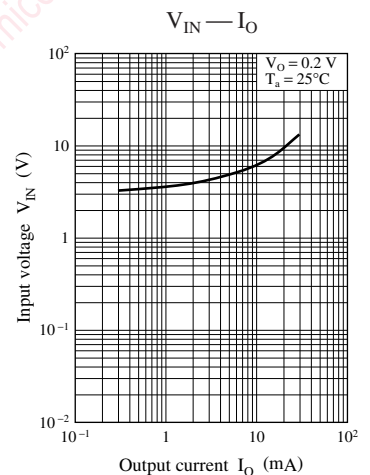
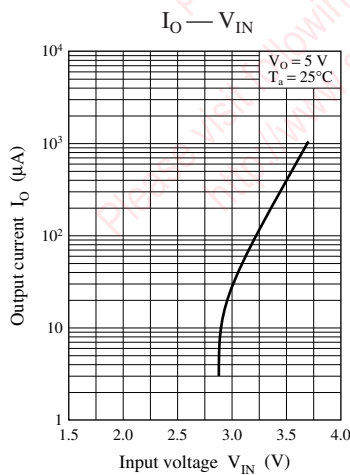
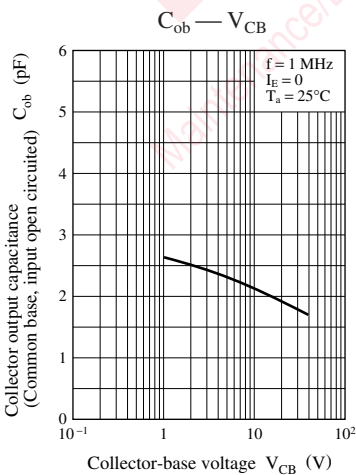
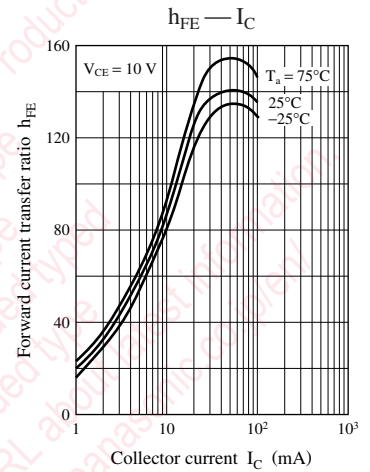
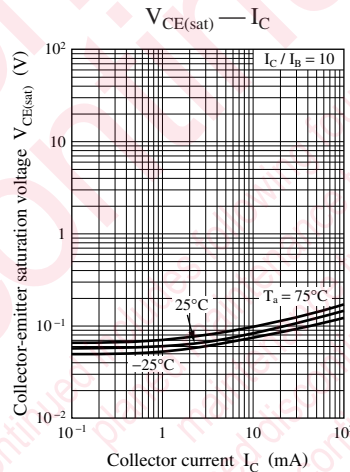
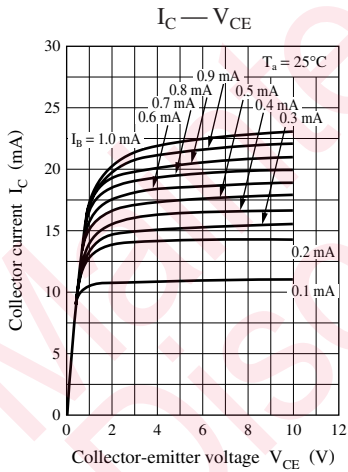


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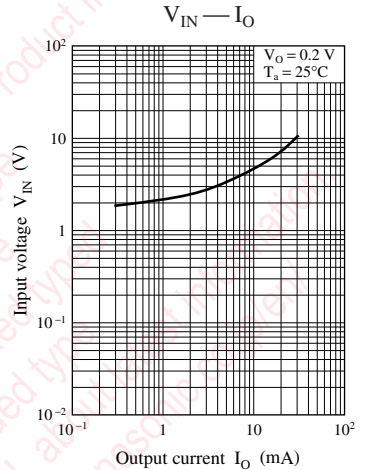
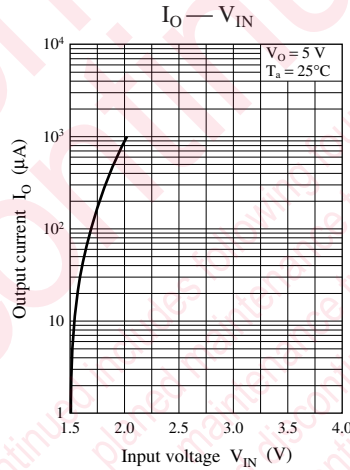
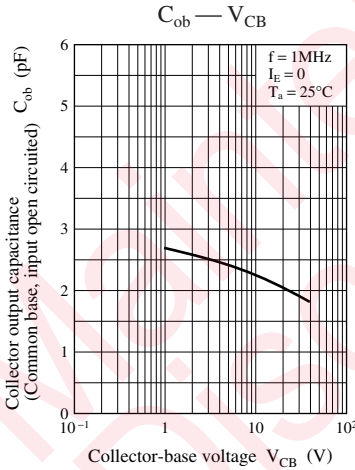
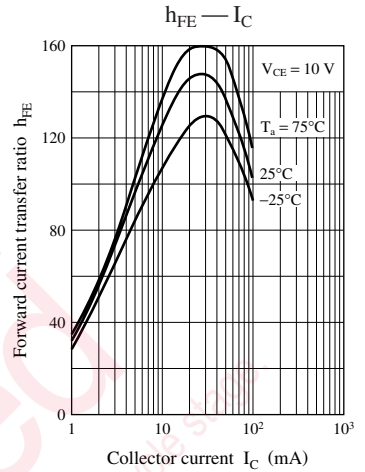
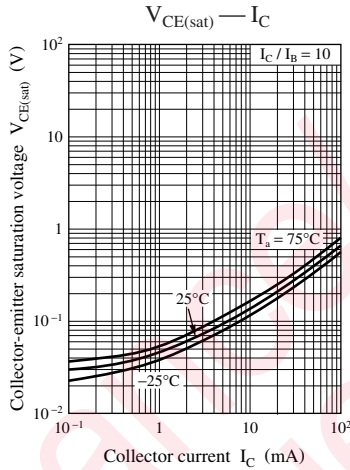
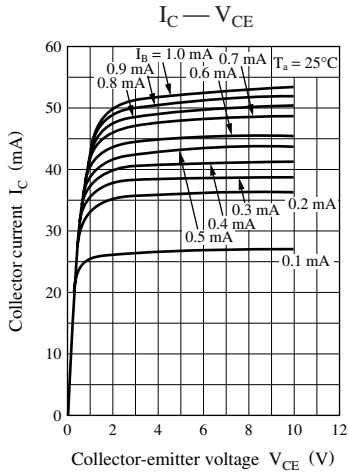




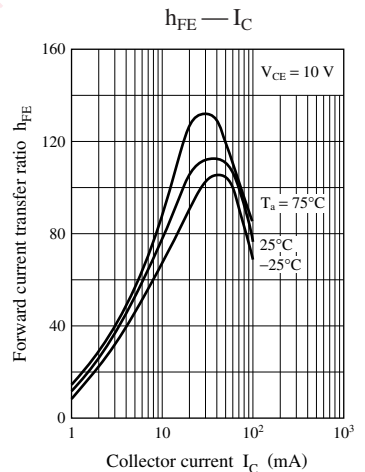
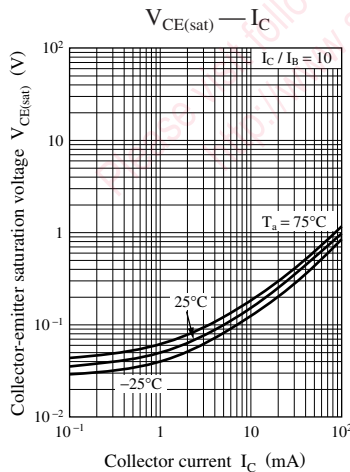
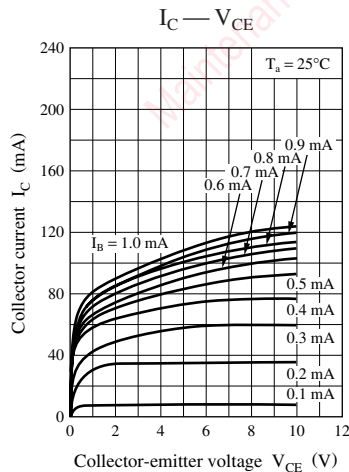
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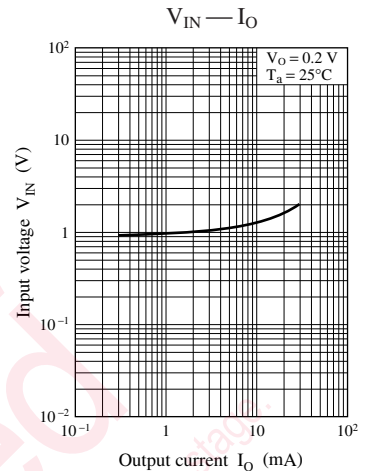
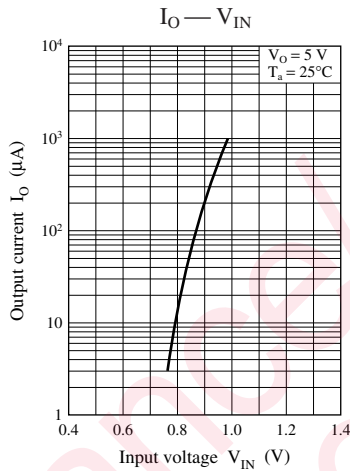
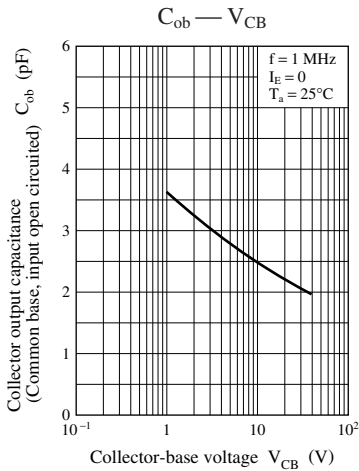


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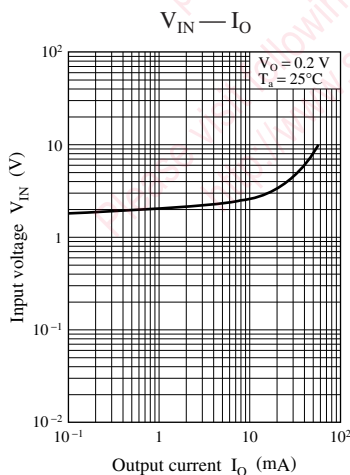
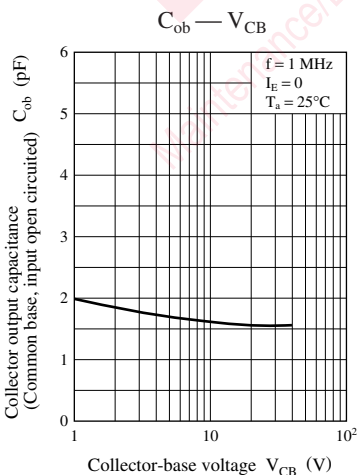
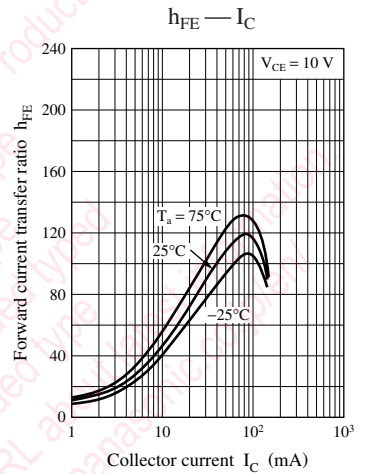
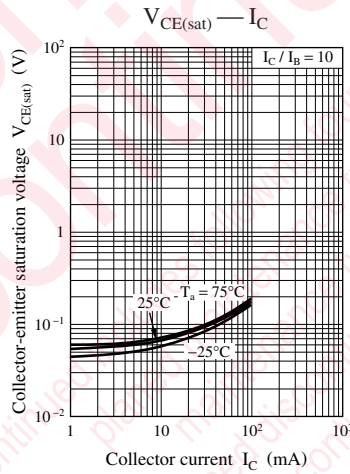
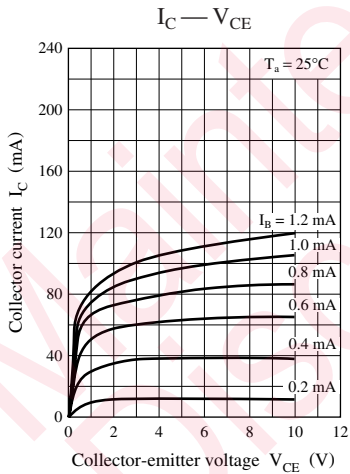


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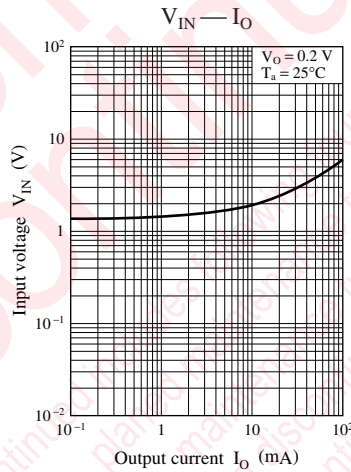
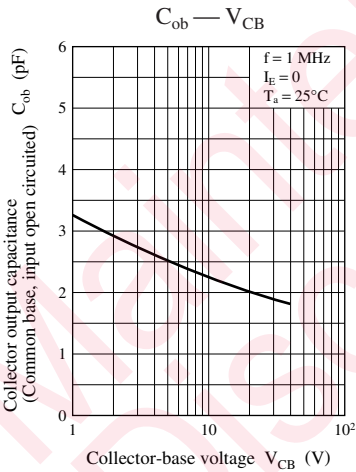
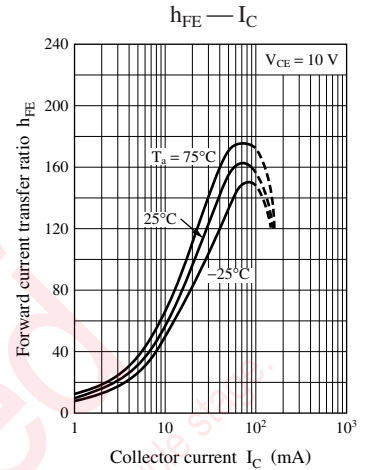
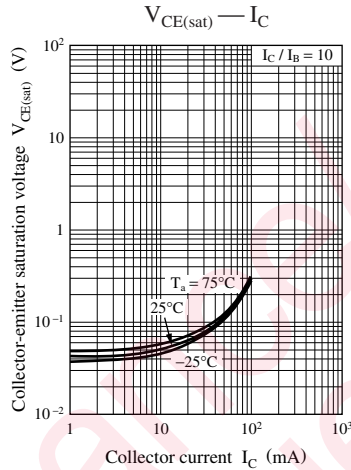
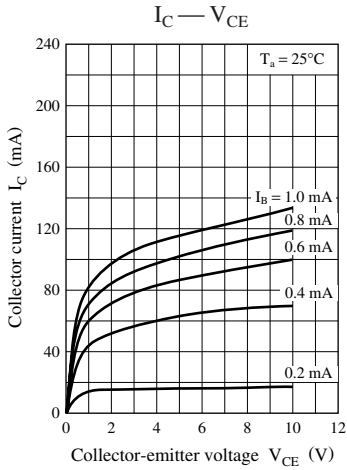




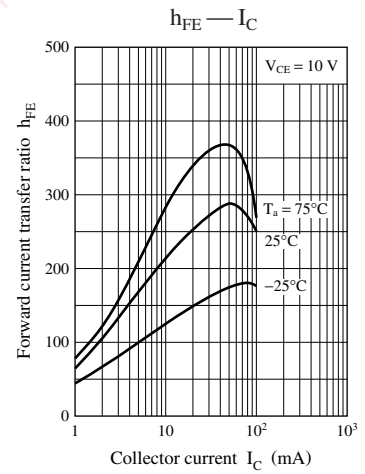
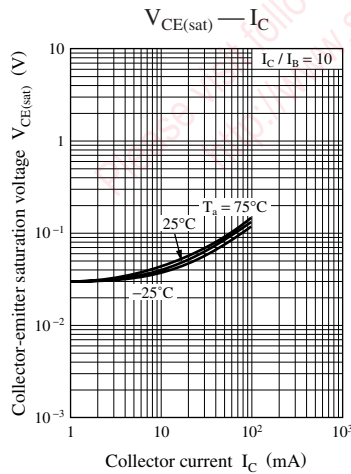
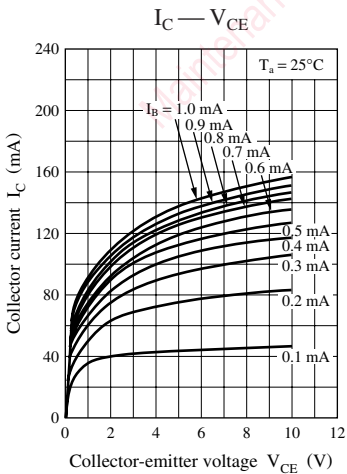
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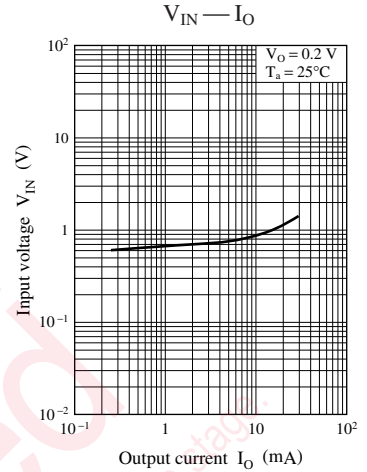
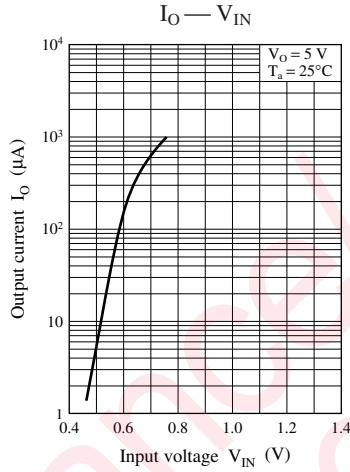
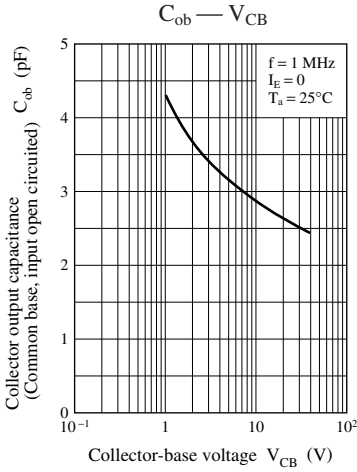


Characteristics charts of UNR521L

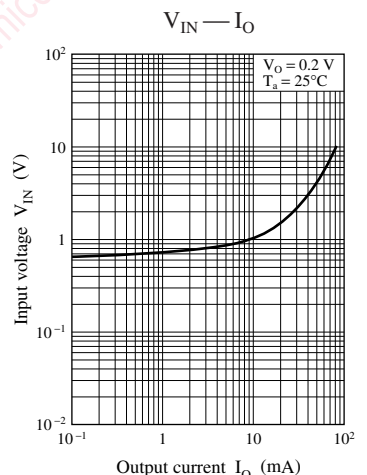
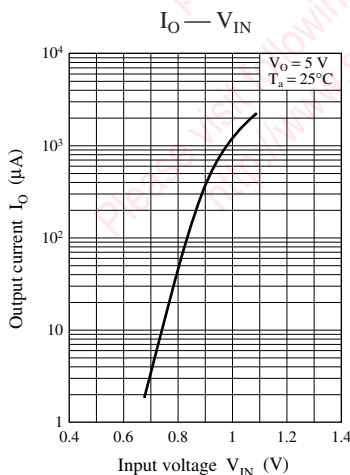
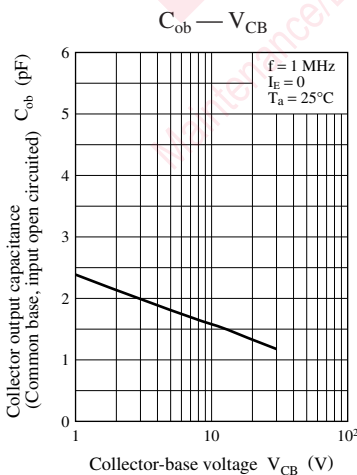
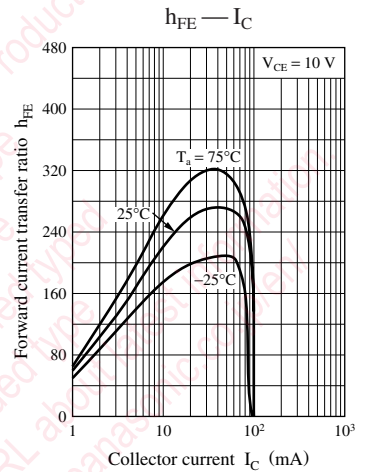
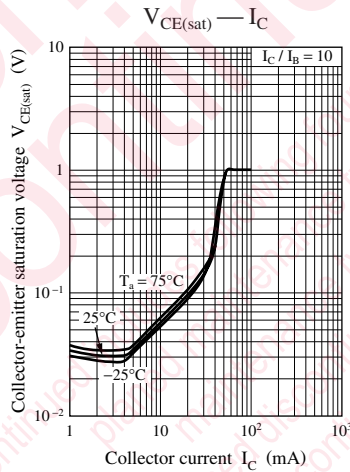
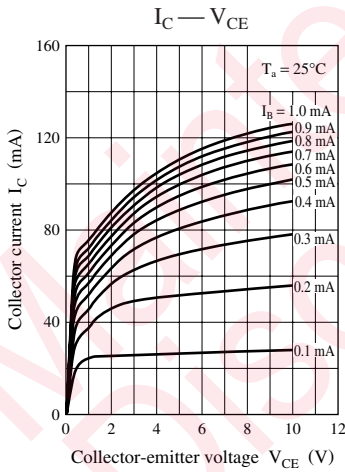


Characteristics charts of UNR521M

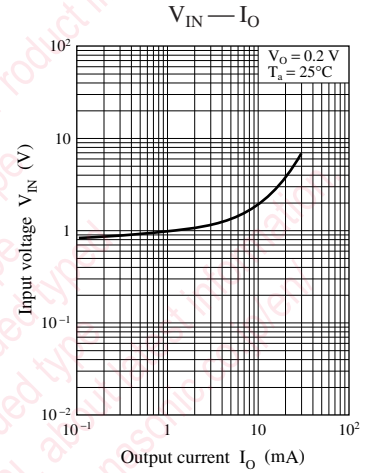
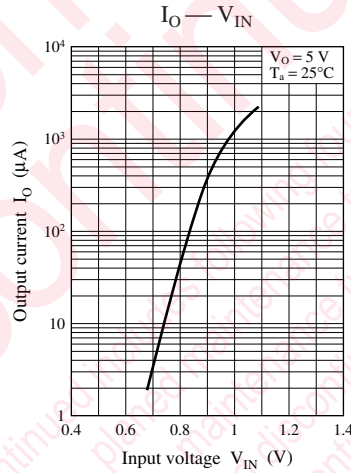
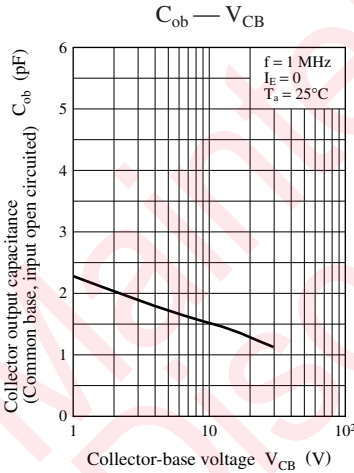
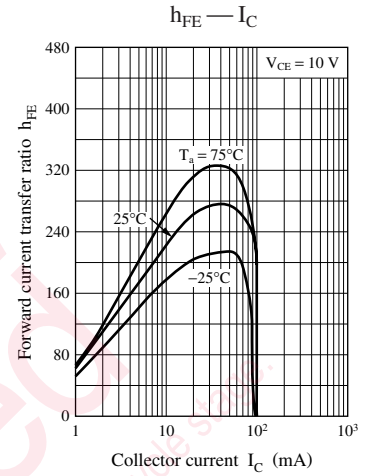
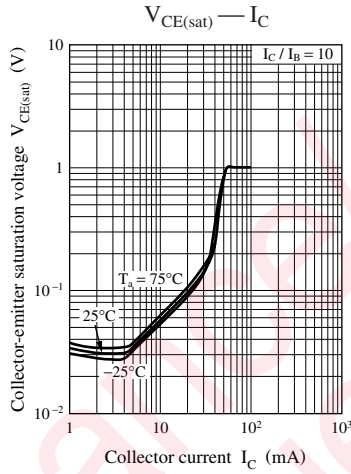
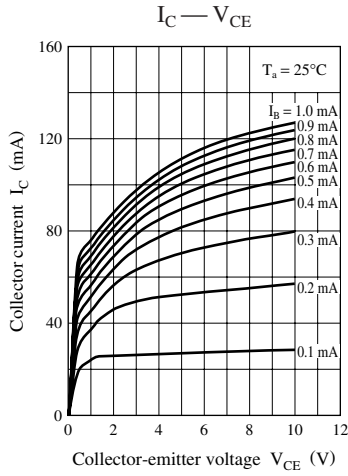




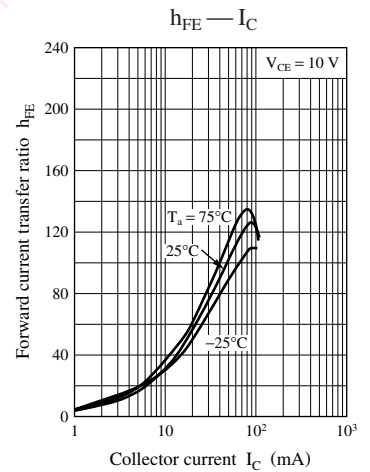
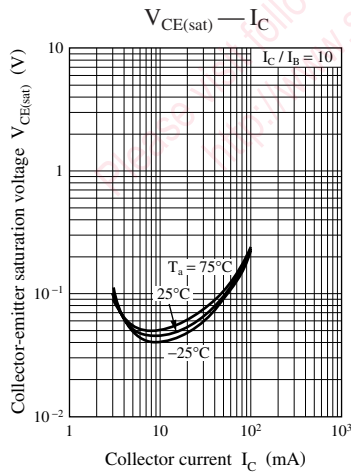
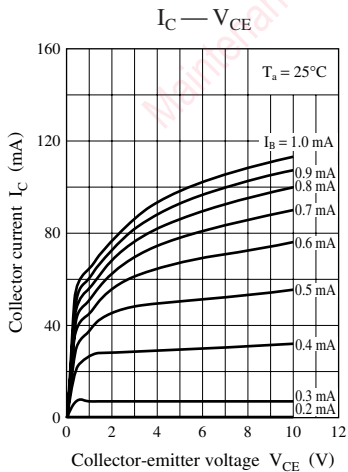
Characteristics charts of UNR521N

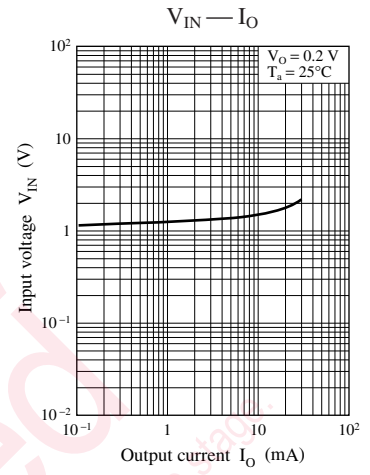
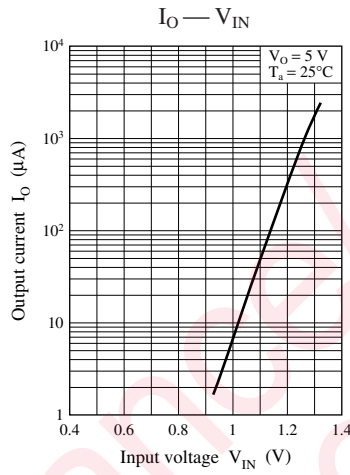
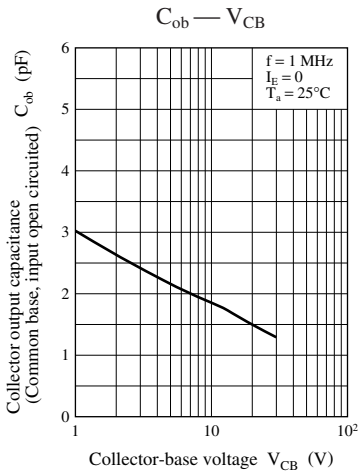


Characteristics charts of UNR521T

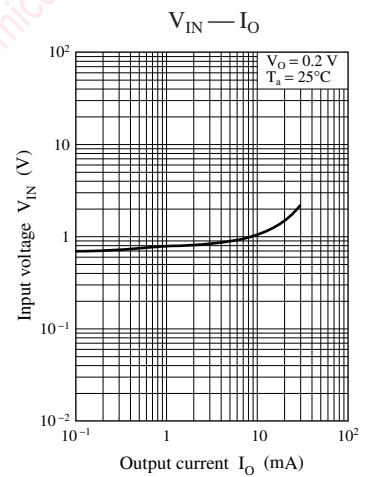
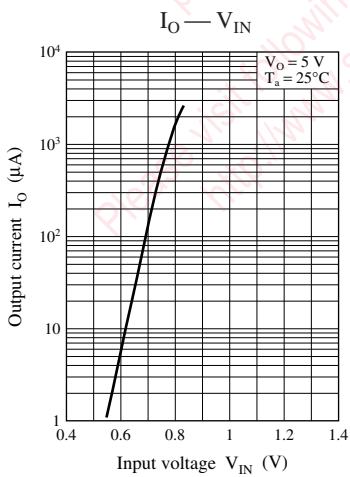
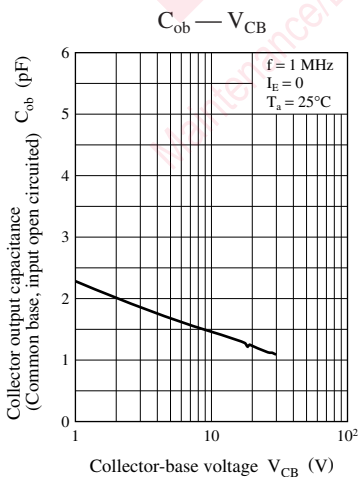
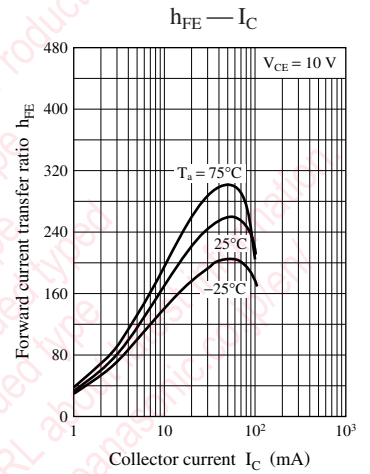
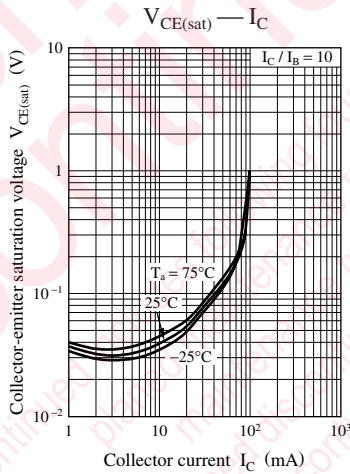
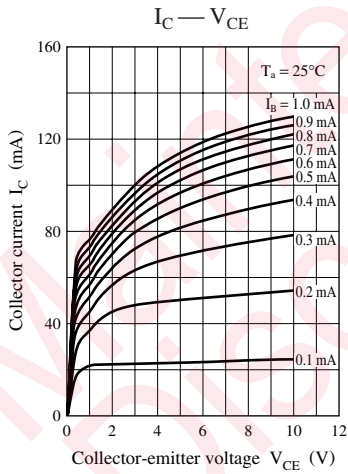


Characteristics charts of UNR521V





Characteristics charts of UNR521Z



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